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CONTENTS

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RAPID COMMUNICATIONS

Electronic structure: wide-band, narrow-band, and strongly correlated systems

- Elimination of Coulomb finite-size effects in quantum many-body simulations R4851
A. J. Williamson, G. Rajagopal, R. J. Needs, L. M. Fraser, W. M. C. Foulkes, Y. Wang, and M.-Y. Chou
- Integer-filling metal-insulator transitions in the degenerate Hubbard model R4855
Marcelo J. Rozenberg
- Spectral functions of one-dimensional models of correlated electrons R4859
Julien Favand, Stephan Haas, Karlo Penc, Frédéric Mila, and Elbio Dagotto

Semiconductors I: bulk

- Infrared spectroscopic study of phonons coupled to charge excitations in FeSi R4863
A. Damascelli, K. Schulte, D. van der Marel, and A. A. Menovsky

Semiconductors II: surfaces, interfaces, microstructures, and related topics

- Resonant photoluminescence of semiconductor microcavities: The role of acoustic phonons
in polariton relaxation R4867
R. P. Stanley, S. Pau, U. Oesterle, R. Houdré, and M. Illegems
- Magneto-optical studies of a single quantum dot: Excited states and spin flip of excitons R4871
W. Heller and U. Bockelmann
- Conductance quantization at room temperature in magnetic and nonmagnetic metallic nanowires R4875
J. L. Costa-Krämer
- Numerical simulation of shell-filling effects in circular quantum dots R4879
M. Macucci, Karl Hess, and G. J. Iafrate
- Dynamics of nonlinear optical properties in $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{InP}$ quantum-well waveguides R4883
C. Cacciatore, L. Faustini, G. Leo, C. Coriasso, D. Campi, A. Stano, and C. Rigo
- Dependence of the energy and form of the optical-absorption onset of interface diffusion in Si_nGe_m
superlattices R4887
I. A. Papadogonas, A. N. Andriotis, and E. N. Economou
- Bulk quantum Hall effect: Evidence that surface states play a key role R4891
S. Hill, P. S. Sandhu, J. S. Qualls, J. S. Brooks, M. Tokumoto, N. Kinoshita, T. Kinoshita, and Y. Tanaka
- Quantitative study of large composite-fermion systems R4895
J. K. Jain and R. K. Kamilla
- Spectromicroscopic evidence of Ge-GaSe chemical reactions: Not a Schottky system R4899
J. Almeida, I. Vobornik, H. Berger, M. Kiskinova, A. Kolmakov, M. Marsi, and G. Margaritondo
- Exact dynamical response of an N -electron quantum dot subject to a time-dependent potential R4903
Simon C. Benjamin and Neil F. Johnson
- Multiphoton photoluminescence from GaN with tunable picosecond pulses R4907
Doseok Kim, I. H. Libon, C. Voelkmann, Y. R. Shen, and V. Petrova-Koch
- Emission dynamics of a magnetoexciton quantum-dot microcavity laser R4910
J. D. Berger, S. Hallstein, O. Lyngnes, W. W. Rühle, G. Khitrova, and H. M. Gibbs

(Continued)

Surface physics, low-dimensional systems, and related topics

Structural changes induced upon charging Ge clusters	R4914
Serdar Ögüt and James R. Chelikowsky	
Grain-size effect on elastic properties of C_{60} films and their relationship to the order-disorder phase transition	R4918
F. Yan, Y. N. Wang, and M. Gu	
Metallic resistivity in crystalline ropes of single-wall carbon nanotubes	R4921
J. E. Fischer, H. Dai, A. Thess, R. Lee, N. M. Hanjani, D. L. Dehaas, and R. E. Smalley	
Breaking of time-reversal symmetry probed by optical second-harmonic generation	R4925
R. Stolle, K. J. Veenstra, F. Manders, Th. Rasing, H. van den Berg, and N. Persat	

ARTICLES**Electronic structure: wide-band, narrow-band, and strongly correlated systems**

Semiclassical description of cyclotron resonance in quasi-two-dimensional organic conductors: Theory and experiment	4931
Stephen Hill	
Thermal properties of the self-interstitial in aluminum: An <i>ab initio</i> molecular-dynamics study	4941
B. J. Jesson, M. Foley, and P. A. Madden	
Ab initio full charge-density study of the atomic volume of α -phase Fr, Ra, Ac, Th, Pa, U, Np, and Pu	4947
L. Vitos, J. Kollár, and H. L. Skriver	
Charge density and charge transfer in stage-1 alkali-graphite intercalation compounds	4953
C. Hartwigsen, W. Witschel, and E. Spohr	
Electronic-oscillator analysis of femtosecond four-wave mixing in conjugated polyenes	4960
T. Meier, S. Tretiak, V. Chernyak, and S. Mukamel	
Temperature dependence of phonon-assisted excitation probability in $Gd Tb(MoO_4)_3$: Evidence for a change in electron-lattice coupling near a structural phase transition	4978
P. Raveendran, N. Sukumar, and T. K. K. Srinivasan	
Magnetic-field-induced phase transition and sliding motion of charge-density waves in η - Mo_4O_{11} crystals	4983
M. Sasaki, Y. Hara, M. Inoue, T. Takamasu, N. Miura, G. Machel, and M. von Ortenberg	
Conductance of nanotube junctions and its scaling law	4991
Ryo Tamura and Masaru Tsukada	
Optical properties of graphite from first-principles calculations	4999
R. Ahuja, S. Auluck, J. M. Wills, M. Alouani, B. Johansson, and O. Eriksson	
Core effects in lithium hydride	5006
L. Bellaiche and K. Kunc	
Dirac-Fock-Slater calculations on the geometric and electronic structure of neutral and multiply charged C_{60} fullerenes	5015
T. Baştuğ, P. Kürpick, J. Meyer, W.-D. Sepp, B. Fricke, and A. Rosén	
Uniqueness of wave-plate measurements in determining the tensor components of second-order surface nonlinearities	5021
Jeffery J. Maki, Martti Kauranen, Thierry Verbiest, and André Persoons	
Integrable supersymmetric t - J model with magnetic impurity	5027
P. Schlottmann and A. A. Zvyagin	

(Continued)

Semiconductors I: bulk

Noble-gas-related defects in Si and the origin of the 1018 meV photoluminescence line	5037
S. K. Estreicher, J. Weber, A. Derecskei-Kovacs, and D. S. Marynick	
Nonlocal pseudopotentials in complex band-structure and photoemission calculations	5045
A. Bödicker and W. Schattke	
Sulfur $L_{2,3}$ and zinc $M_{2,3}$ soft-x-ray fluorescence spectra in CdS and ZnS	5051
L. Zhou, T. A. Callcott, J. J. Jia, D. L. Ederer, and Rupert Perera	
Thermal relaxation of excitons in ZnSe and $Zn_{1-x}Mn_x$ Se diluted magnetic semiconductors	5062
C. D. Poweleit, L. M. Smith, and B. T. Jonker	
Remote and spatially separated D^- centers in quasi-two-dimensional semiconductor structures	5065
I. K. Marmorkos, V. A. Schweigert, and F. M. Peeters	
Determination of electric-field gradients in semiconductors with high precision and high sensitivity	5073
Gert Denninger and Daniel Reiser	
Electric-field-induced luminescence quenching in an electroluminescent organic semiconductor	5079
S. Tasch, G. Kranzelbinder, G. Leising, and U. Scherf	
Quasiparticle transport equation with collision delay. I. Phenomenological approach	5084
Václav Špička, Pavel Lipavský, and Klaus Morawetz	
Quasiparticle transport equation with collision delay. II. Microscopic theory	5095
Václav Špička, Pavel Lipavský, and Klaus Morawetz	
Green's function description of momentum-orientation relaxation of photoexcited electron plasmas in semiconductors	5110
R. Binder, H. S. Köhler, M. Bonitz, and N. Kwong	
Lattice vibrations and phonon-plasmon coupling in Raman spectra of p -type $In_{0.53}Ga_{0.47}As$	5117
A. M. Mintairov and H. Temkin	

Semiconductors II: surfaces, interfaces, microstructures, and related topics

Electronic structures and optical-absorption spectra of hydrogen-terminated Si quantum slabs	5124
San-huang Ke, Kai-ming Zhang, and Xi-de Xie	
Surface character in the experimental Fermi surface of epitaxial $ErSi_{1.7}$ (0001) by photoemission spectroscopy	5129
J. A. Martín-Gago, J. Y. Veuillen, C. Casado, and T. A. Nguyen Tan	
Surface atomic structure of epitaxially grown erbium silicide films on $Si(111)7\times7$	5136
J. A. Martín-Gago, J. M. Gómez-Rodríguez, and J. Y. Veuillen	
Quantum corrections to the conductivity of fermion gauge-field models: Application to the half-filled Landau level	5141
A. D. Mirlin and P. Wölfle	
Many-body carrier interaction effects in quantum wells	5147
Alfred Kahan and Lionel Friedman	
Theory of exciton pair states and their nonlinear optical properties in semiconductor quantum dots	5153
Selvakumar V. Nair and Toshihide Takagahara	
Direct observation of the LO phonon bottleneck in wide $GaAs/Al_xGa_{1-x}As$ quantum wells	5171
B. N. Murdin, W. Heiss, C. J. G. M. Langerak, S.-C. Lee, I. Galbraith, G. Strasser, E. Gornik, M. Helm, and C. R. Pidgeon	
In-plane magnetic field studies of $InAs/GaSb$ superlattices	5177
A. R. Rundell, G. P. Srivastava, and J. C. Inkson	
Excitons in CdSe quantum dots	5184
U. E. H. Laheld and G. T. Einevoll	
Exact density of states of the lowest Landau level in a $spin-\frac{1}{2}$ system with uncorrelated disorders	5205
Ming-Hsien Tu and Min-Fong Yang	

(Continued)

Bound states of two particles confined to parallel two-dimensional layers and interacting via dipole-dipole or dipole-charge laws	5214
V. I. Yudson, M. G. Rozman, and P. Reineker	
Experimental determination of the electrical band-gap energy of porous silicon and the band offsets at the porous silicon/crystalline silicon heterojunction	5220
F. P. Romstad and E. Veje	
Quasisteady space-charge fields in photorefractive multiple quantum wells: Edge effects	5226
María Aguilar, M. Carrascosa, F. Agulló-López, L. Solymar, and L. F. Magaña	
Effects of band offset and nonparabolicity on the effective mass of two-dimensional electron gases in modulation- δ -doped $\text{Ga}_{0.47}\text{In}_{0.53}\text{As}$ -based heterostructures	5235
Y. T. Dai, Y. F. Chen, and I. Lo	
Influence of composition fluctuations in $\text{Al}(\text{Ga})\text{As}$ barriers on the exciton localization in thin GaAs quantum wells	5239
M. Ramsteiner, R. Hey, R. Klann, U. Jahn, I. Gorbunova, and K. H. Ploog	
Electro-optical properties of semiconductor superlattices in the regime of Franz-Keldysh oscillations	5243
Gerard Czajkowski, Marco Dressler, and Franco Bassani	
Microroughness and exciton localization in $(\text{Al,Ga})\text{As}/\text{GaAs}$ quantum wells	5253
R. Grousson, V. Voliotis, N. Grandjean, J. Massies, M. Leroux, and C. Deparis	
Nonlinear transport in steady-state terahertz-driven two-dimensional electron gases	5259
W. Xu and C. Zhang	
Closed-form solutions to surface Green's functions	5266
A. Umerski	
Structural ordering and interface morphology in symmetrically strained $(\text{GaIn})\text{As}/\text{Ga}(\text{PAs})$ superlattices grown on off-oriented $\text{GaAs}(100)$	5276
C. Giannini, L. Tapfer, Y. Zhuang, L. De Caro, T. Marschner, and W. Stolz	
Binding of biexcitons in $\text{GaAs}/\text{Al}_x\text{Ga}_{1-x}\text{As}$ superlattices	5284
V. Mizeikis, D. Birkedal, W. Langebein, V. G. Lyssenko, and J. M. Hvam	
$1/f$ noise in δ -doped GaAs analyzed in terms of mobility fluctuations	5290
X. Y. Chen, P. M. Koenraad, F. N. Hooge, J. H. Wolter, and V. Aninkevicius	
Compressibility, capacitance, and ground-state energy fluctuations in a weakly interacting quantum dot	5297
R. Berkovits and B. L. Altshuler	
Orthogonal localized wave functions of an electron in a magnetic field	5306
E. I. Rashba, L. E. Zhukov, and A. L. Efros	
Origin of pair-tunneling states in semiconductor quantum dots	5313
Yi Wan, Gerardo Ortiz, and Philip Phillips	
Elastic scattering and absorption of surface acoustic waves by a quantum dot	5325
Andreas Knäbchen, Yehoshua B. Levinson, and Ora Entin-Wohlman	
Resonant transport properties of tight-binding mesoscopic rings	5337
Jingbo Li, Zhao-Qing Zhang, and Youyan Liu	

Surface physics, low-dimensional systems, and related topics

Influence of the data base and algorithmic parameters on the image quality in holographic diffuse LEED	5344
K. Reuter, H. Wedler, M. Ott, K. Heinz, J. A. Vamvakas, X. Chen, and D. K. Saldin	
Indium-induced $\text{Si}(111)4\times 1$ silicon substrate atom reconstruction	5353
A. A. Saranin, E. A. Khramtsova, K. V. Ignatovich, V. G. Lifshits, T. Numata, O. Kubo, M. Katayama, I. Katayama, and K. Oura	
Role of corner holes in $\text{Si}(111)-7\times 7$ structural formation studied by HBO_2 molecular irradiation and quenching	5360
Koji Miyake, Masahiko Ishida, Kenji Hata, and Hidemi Shigekawa	

Atomic and electronic structure of the diamond (100) surface: Reconstructions and rearrangements at high hydrogen coverage	5364
M. D. Winn, M. Rassinger, and J. Hafner	
Core-level spectroscopic study of the evolution of the sulfur-passivated InP(001) surface during annealing	5376
Z. Tian, M. W. C. Dharma-wardana, Z. H. Lu, R. Cao, and L. J. Lewis	
Surface reconstructions of In on Si(111)	5384
J. Kraft, M. G. Ramsey, and F. P. Netzer	
Structure determination of two-dimensional adenine crystals on graphite	5394
J. E. Freund, M. Edelwirth, P. Kröbel, and W. M. Heckl	
Low-energy electron thermal diffuse scattering from Al(111) individually resolved in energy and momentum	5398
V. Zielasek, A. Büssenschütt, and M. Henzler	
Electronic structure of two-dimensional magnetic alloys: $c(2 \times 2)$ Mn on Cu(100) and Ni(100)	5404
O. Rader, W. Gudat, C. Carbone, E. Vescovo, S. Blügel, R. Kläsches, W. Eberhardt, M. Wuttig, J. Redinger, and F. J. Himpsel	
Conductance quantization in nanowires formed between micro and macroscopic metallic electrodes	5416
J. L. Costa-Krämer, N. García, P. García-Mochales, P. A. Serena, M. I. Marqués, and A. Correia	
Decoupling and testing of the generalized Ohm's law	5425
Ronit Levy-Nathansohn and David J. Bergman	
Three-dimensional electron momentum densities: A comparison of $(\gamma, e\gamma)$ and $(e, 2e)$ spectroscopies	5440
F. F. Kurp, M. Vos, Th. Tschentscher, A. S. Kheifets, J. R. Schneider, E. Weigold, and F. Bell	
Spectroscopic behavior of halogen photodesorption from alkali halides under UV and VUV excitation	5448
N. Zema, M. Piacentini, P. Czuba, J. Kolodziej, P. Piatkowski, Z. Postawa, and M. Szymonski	
Auger photoelectron coincidence spectroscopy studies: Trends in the $L_{2,3}$ - $M_{4,5}$ line shapes across the 3d transition-metal series	5455
C. P. Lund, S. M. Thurgate, and A. B. Wedding	
Theoretical study of the valence-level photoemission spectrum of C_2H_4 adsorbed on a Ni metal surface	5466
M. Ohno and W. von Niessen	
Angular distribution of photoelectrons emitted from noncrystalline solids	5478
Y. F. Chen	
Electronic shell energies and deformations in large sodium clusters from evaporation spectra	5485
F. Chandezon, S. Björnholm, J. Borggreen, and K. Hansen	
Nonlinear friction in the periodic stick-slip motion of coupled oscillators	5491
Y. Braiman, F. Family, and H. G. E. Hentschel	
Theory of photoemission from the Ni 2p core level	5505
J. G. Menchero	
Cumulative Author Index	5517